



Crystal size	~1cm or larger in size
Dopants	Undoped (intrinsic semiconductor)
Material properties	1.56 eV emission (300K), direct gap semiconductor
Crystal structure	γ -rhombohedral semiconducting
Unit cell parameters	$a = b = 0.400$ nm, $c = 2.492$ nm
Growth method	Bridgman growth technique [Optional: Chemical vapor transport or flux zone]
Purity	99.9999 % confirmed

